

Active

L1: (3796) (opening trench via hole recess) with ((plasma gas) near (h2 hydrogen))

L2: (78) 1 and (opening trench via hole recess) with ((plasma gas) near (chlorine))

L6: (2) 5 and (opening trench via hole recess) with (silicide)

L5: (18) 2 and (opening trench via hole recess) with (insulat\$3 dielectric)

Failed

Search

US-PG-FUE;USPAT;EPO;JPO

Default operator: JOR

☐ Search
☐ Highlight all hit items initially

2 and (opening trench via hole recess) with (insulat\$3 dielectric)

ERS form

ISAR form

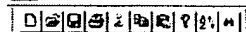
Image

Text

HTML

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	4
1	<input type="checkbox"/>	US 2005003757.7	2005021		Method of fabricating semiconductor device	438/270			Numazawa, Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	US 2004016665.6	2004082		METHOD OF FABRICATING SEMIC	438/589	257/E21.4		Numazawa, Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	US 2003012480.3	2003070		Method of fabricating semiconductor device	438/270	257/E21.4		Numazawa, Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	US 2003001331.6	2003011	23	Process for fabricating semiconductor device	438/706	257/E21.2		Negishi, Nobuyuki et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	US 2002009865.5	2002072		Method of fabricating semiconductor device	438/270	257/E21.4		Numazawa, Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	US 2002000986.4	2002012		Method of fabricating semiconductor device	438/589	257/288;		Numazawa, Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	US 6803281 B2	2004101		Method of fabricating semiconductor device	438/270	257/288;		Numazawa; Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
8	<input type="checkbox"/>	US 6720220 B2	2004041		Method of fabricating semiconductor device	438/270	257/288;		Numazawa; Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
9	<input type="checkbox"/>	US 6645870 B2	2003111	21	Process for fabricating semiconductor device	438/710	257/E21.2		Negishi; Nobuyuki et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
10	<input type="checkbox"/>	US 6512265 B2	2003012		Method of fabricating semiconductor device	257/330	257/288;		Numazawa; Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
11	<input type="checkbox"/>	US 6410959 B2	2002062		Method of fabricating semiconductor device	257/330	257/341;		Numazawa; Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
12	<input type="checkbox"/>	US 6307231 B1	2001102		Method of fabricating semiconductor device	257/330	257/341;		Numazawa; Sumito et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

Ready



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Failed

Search: List Browse Runout Gear

DB: US-PG-PUB; USPAT; EPC; IPO ☐ Durab ☐ Highlight all hits (some locally)

Default operator: [OR]

2 and (opening trench via hole recess) with (insulat\$3 dielectric)

ERS form ISAR form Image Text HTML

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	4	5
7	☞	US 6803281	2004101		Method of fabricating semiconductor device	438/270	257/288;		Numazawa; Sumito et al.	☞	☞	☞	☞	☞	☞	☞
8	☞	US 6720220	2004041		Method of fabricating semiconductor device	438/270	257/288;		Numazawa; Sumito et al.	☞	☞	☞	☞	☞	☞	☞
9	☞	US 6645870	2003111	21	Process for fabricating semiconductor device	438/710	257/328;		Negishi; Nobuyuki et al.	☞	☞	☞	☞	☞	☞	☞
10	☞	US 6512265	2003012		Method of fabricating semiconductor device	257/330	257/288;		Numazawa; Sumito et al.	☞	☞	☞	☞	☞	☞	☞
11	☞	US 6410959	2002062		Method of fabricating semiconductor device	257/330	257/328;		Numazawa; Sumito et al.	☞	☞	☞	☞	☞	☞	☞
12	☞	US 6307231	2001102		Method of fabricating semiconductor device	257/330	257/341;		Numazawa; Sumito et al.	☞	☞	☞	☞	☞	☞	☞
13	☞	US 6168996	2001010		Method of fabricating semiconductor device	438/270	257/342;		Numazawa; Sumito et al.	☞	☞	☞	☞	☞	☞	☞
14	☞	US 5458858	1995101		Integrated procedure for high yield production of	422/234	257/330;		Dawkins; John L.	☞	☞	☞	☞	☞	☞	☞
15	☞	US 5324497	1994062		Integrated procedure for high yield production of	423/478	422/200;		Westerlund; G. Oscar	☞	☞	☞	☞	☞	☞	☞
16	☞	US 4935800	1990061		Semiconductor integrated circuit	257/520	204/277;		Taguchi; Minoru	☞	☞	☞	☞	☞	☞	☞
17	☞	JP 2001126989	2001051		METHOD OF FORMING SEMICOND		204/278;		ODA, KATSUYA	☞	☞	☞	☞	☞	☞	☞
18	☞	JP 04286115.A	1992101		MANUFACTURE OF SEMICONDUCTOR DE		257/501;		SHIOTANI, YOSHIMI et al.	☞	☞	☞	☞	☞	☞	☞